

# BD375/377/379

# **Medium Power Linear and Switching Applications**

Complement to BD376, BD378 and BD380 respectively



# **NPN Epitaxial Silicon Transistor**

# **Absolute Maximum Ratings** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage : BD375	50	V	
	: BD377	75	V	
	: BD379	100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage : BD375	45	V	
	: BD377	60	V	
	: BD379	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current (DC)	2	Α	
СР	*Collector Current (Pulse)	3	А	
В	Base Current	1	А	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	25	W	
Γ <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C	

# $\textbf{Electrical Characteristics} \ \, \textbf{T}_{\text{C}} = 25 \, ^{\circ} \text{C unless otherwise noted}$

Symbol	Paramet	er	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaini	ng Voltage					
		: BD375	$I_C = 100 \text{mA}, I_B = 0$	45			V
		: BD377		60			V
		: BD379		80			V
BV <sub>CBO</sub>	Collector-Base	: BD375	$I_C = 100 \mu A, I_E = 0$	50			V
	Breakdown Voltage	: BD377		75			V
		: BD379		100			V
I <sub>CBO</sub>	Collector Cut-off Current	: BD375	$V_{CB} = 45V, I_{E} = 0$			2	μΑ
		: BD377	$V_{CB} = 60V, I_{E} = 0$			2	μΑ
		: BD379	$V_{CB} = 80V, I_{E} = 0$			2	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current		$V_{EB} = 5V, I_{C} = 0$			100	μΑ
h <sub>FE1</sub>	* DC Current Gain		$V_{CE} = 2V, I_{C} = 0.15A$	40		375	
h <sub>FE2</sub>			$V_{CE} = 2V, I_{C} = 1A$	20			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturati	on Voltage	$I_C = 1A, I_B = 0.1A$			1	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage		$V_{CE} = 2V$ , $I_C = 1A$			1.5	V
t <sub>ON</sub>	Turn ON Time		$V_{CC} = 30V, I_{C} = 0.5A$		50		ns
t <sub>OFF</sub>	Turn OFF Time		$I_{B1} = -I_{B2} = 0.05A$ $R_{L} = 60\Omega$		500		ns

<sup>\*</sup> Pulse Test: PW=350µs, duty Cycle=2% Pulsed

# **h**<sub>FE</sub> Classification

Classification	6	10	16	25
h <sub>FE1</sub>	40 ~ 100	63 ~ 160	100 ~ 250	150 ~ 375

# **Typical Characteristics**

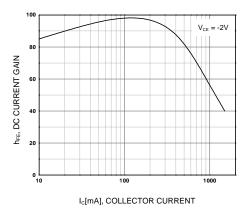


Figure 1. DC current Gain

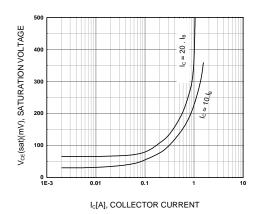


Figure 2. Collector-Emitter Saturation Voltage

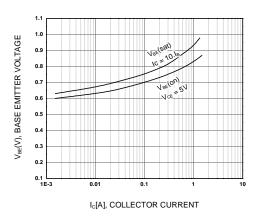


Figure 3. Base-Emitter Voltage

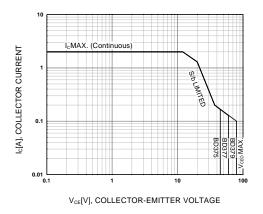


Figure 4. Safe Operating Area

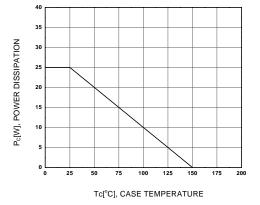
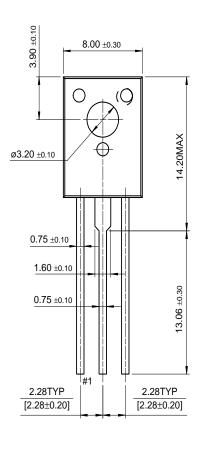
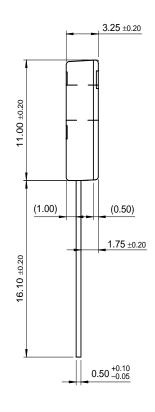


Figure 5. Power Derating

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Dimensions in Millimeters

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